



40V DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} MAX	l _D T _A = +25°C
40V	24mΩ @V _{GS} = 10V	9.0A
40 V	32mΩ @V _{GS} = 4.5V	7.8A

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

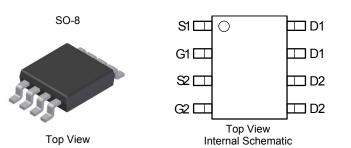
- Motor Control
- Backlighting
- Power Management Functions
- DC-DC Converters

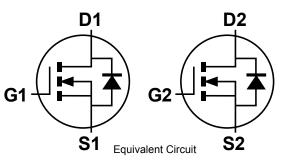
Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram below
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.074 grams (approximate)





Ordering Information (Note 4 & 5)

Part Number	Compliance	Case	Packaging
DMN4026SSD-13	Standard	SO-8	2,500/Tape & Reel
DMN4026SSDQ-13	Automotive	SO-8	2,500/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

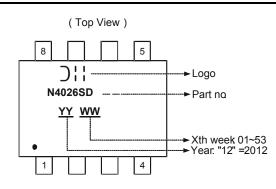
 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information





Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V _{DSS}	40	V		
Gate-Source Voltage	V _{GSS}	±20	V		
	Steady State	T _A = +25°C T _A = +70°C	ID	7.0 5.6	A
Continuous Drain Current (Note 7) V _{GS} = 10V	T<10s	T _A = +25°C T _A = +70°C	ID	9.0 7.2	А
Maximum Continuous Body Diode Forward Curre	I _S	2.5	А		
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	70	A

Thermal Characteristics

Characteristic	Symbol	Value	Units		
Total Dower Dissinction (Note 6)	T _A = +25°C	D	1.3	W	
Total Power Dissipation (Note 6)	T _A = +70°C	PD	0.8		
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Р	98	°C/W	
member (Note 6)	t<10s	R _{θJA}	59		
Total Power Dissipation (Note 7)	T _A = +25°C	D	1.8	W	
Total Fower Dissipation (Note 7)	T _A = +70°C	PD	1.1	vv	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	Devi	71	°C/W	
	t<10s	R _{0JA}	43		
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	11.8			
Operating and Storage Temperature Range		T _{J.} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	1 - 1						
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	—	V	V _{GS} = 0V, I _D = 250µA	
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} = 40V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(th)}	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance			15	24	mΩ	V _{GS} = 10V, I _D = 6A	
Static Drain-Source On-Resistance	R _{DS(ON)}		20	32		V _{GS} = 4.5V, I _D = 5A	
Diode Forward Voltage	V _{SD}		0.7	1.0	V	V _{GS} = 0V, I _S = 1.0A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	1060	_			
Output Capacitance	Coss		84	—	pF	V _{DS} = 20V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}		58	_			
Gate Resistance	R _G		1.6	_	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz	
Total Gate Charge (V _{GS} = 4.5V)	Qg		8.8	20			
Total Gate Charge (V _{GS} = 10V)	Qg	_	19.1	43	nC	V _{DS} = 20V, I _D = 8A	
Gate-Source Charge	Q _{gs}		3.0	7.5	nc		
Gate-Drain Charge	Q _{gd}		2.5	6			
Turn-On Delay Time	t _{D(on)}		5.3	_			
Turn-On Rise Time	tr		7.1	—	nS	$V_{DD} = 25V, R_L = 2.5\Omega$ $V_{GS} = 10V, R_G = 3\Omega$	
Turn-Off Delay Time	t _{D(off)}		15.1	_			
Turn-Off Fall Time	t _f		4.8	_	1		
Body Diode Reverse Recovery Time	t _{rr}		10.5	—	nS	I _F = 8A, di/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q _{rr}		4.15	_	nC	I _F = 8A, di/dt = 100A/µs	

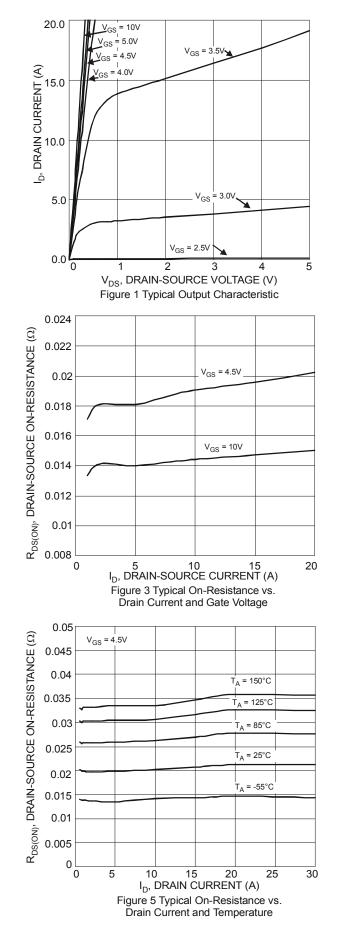
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. Notes:

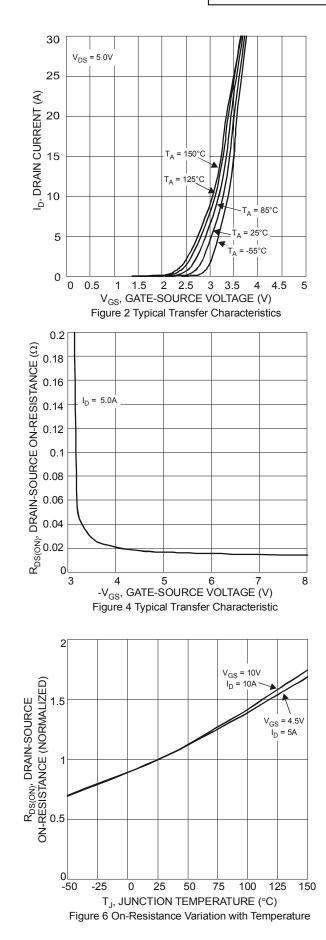
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

DMN4026SSD



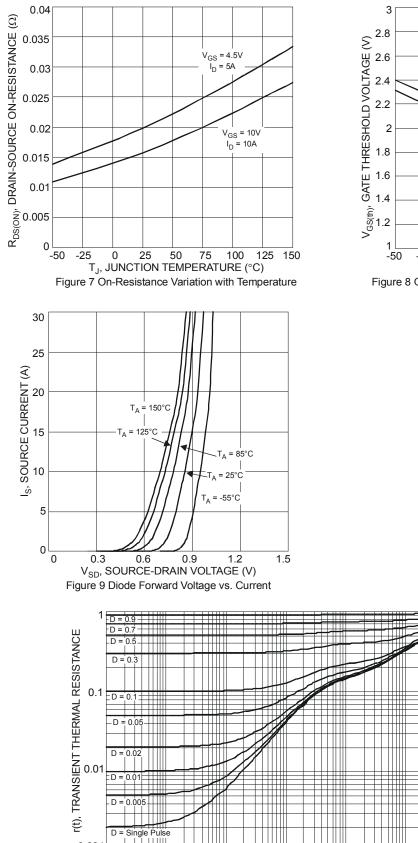


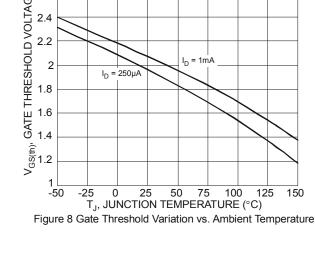


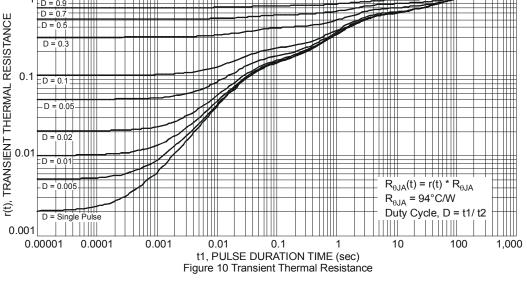
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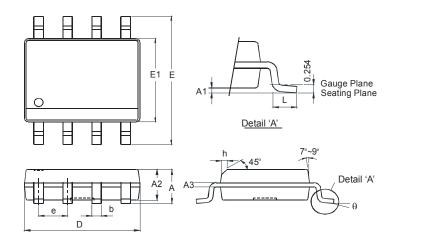






Package Outline Dimensions

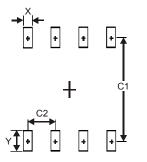
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SO-8					
Dim	Min Max				
Α	-	1.75			
A1	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85 3.95				
е	е 1.27 Тур				
h	- 0.35				
L	0.62	0.82			
θ	0°	8°			
All Di	All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)			
Х	0.60			
Y	1.55			
C1	5.4			
C2	1.27			



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